

T-33-31

PNP Transistor

6501130 NATL SEMICOND, (DISCRETE)

28C 35465 D



DARLINGTON

Type No.	Case Style	V <sub>CEO</sub> (V) Min	V <sub>CE0</sub> (V) Min	VEBO (V) Min	ICES* (μA) Max	ICEX* (V) Max	hFE Min	hFE Max	IC (A) @	VCE (V)	VCE(SAT) (V) Max	VBE(SAT) (V) Min	IC (A) @	C <sub>ob</sub> (pF) Max	f <sub>T</sub> (MHz) Min	f <sub>T</sub> (MHz) Max	IC (A) @	Process No.
D41K1	TO-202 (55)	30*	30*	13	0.5	30	10,000	1000	0.2	5	1.5	2.5	1.5		100	0.02	61	
D41K2	TO-202 (55)	50*	50*	13	0.5	50	10,000	1000	0.2	5	1.5	2.5	1.5		100	0.02	61	
D41K3	TO-202 (55)	30*	30*	13	0.5	30	10,000	1000	0.2	5	1.5	2.5	1		100	0.02	61	
D41K4	TO-202 (55)	50*	50*	13	0.5	50	10,000	1000	0.2	5	1.5	2.5	1		100	0.02	61	
MPSA62	TO-92 (92)	20*	20*		0.1	15	20,000		10	5	1.0		10			0.01	61	
MPSA63	TO-92 (92)	30*	30*		0.1	30	10,000	5000	100	5	1.5		100		125	0.01	61	
MPSA64	TO-92 (92)	30*	30*		0.1	30	20,000	10,000	100	5	1.5		100		125	0.01	61	
MPSA65	TO-92 (92)	30*	30*		0.1	30	20,000	4000	0.1	5	1.5				100	0.01	61	
MPSA66	TO-92 (92)	30*	30*		0.1	30	75,000	40,000	0.1	5	1.5				100	0.01	61	
NSDU95	TO-202 (55)	50	50	10			25,000	15,000	0.2	5	1.5		1		50	0.02	61	
NSDU95A	TO-202 (55)	60	60	10			15,000	4000	0.5	5	1.5				50	0.02	61	
2N6034	TO-126	40	40		500	40	100	750	4	3	2.0		2	200	25	0.75	5J	
2N6035	TO-126	60	60		500	60	100	500	0.05	3	3.0	4.0	4	200	25	0.75	5J	
2N6036	TO-126	80	80		500	80	100	750	4	3	2.0		2	200	25	0.75	5J	
2N6040	TO-220	60	60		500†	60	1000	20,000	4	4	2.0		4	300			5J	
2N6041	TO-220	80	80		500†	80	1000	20,000	4	4	2.0		4	300			5J	
MJE700	TO-126	60	60		200	60	750	150	1.5	3	2.5		1.5		1	1.5	5J	
MJE701	TO-126	60	60		200	60	750	2	3	2.8			2		1	1.5	5J	
MJE702	TO-126	80	80		200	80	750	1.5	1.5	3	2.5		1.5		1	1.5	5J	
MJE703	TO-126	80	80		200	80	750	2	2	3	2.8		2		1	1.5	5J	

T-33-31

6501130 NATL SEMICOND, (DISCRETE)

28C 35466

D

**DARLINGTON (Continued)**

Type No.	Case Style	V <sub>CB0</sub> (V) Min	V <sub>CE0</sub> (V) Min	V <sub>EB0</sub> (V) Min	I <sub>CEX</sub> <sup>†</sup> (μA) Max	I <sub>CB</sub> (V) @ I <sub>CEX</sub> <sup>†</sup>	hFE Min	hFE Max	I <sub>C</sub> (A) @ V <sub>CE</sub> & V <sub>BE(SAT)</sub> (V) Min	V <sub>CE(SAT)</sub> (V) Max	V <sub>BE(SAT)</sub> (V) Min	I <sub>C</sub> (A) @ V <sub>BE(SAT)</sub> (V) Min	C <sub>ob</sub> (pF) Max	f <sub>T</sub> (MHz) Min	f <sub>T</sub> (MHz) Max	I <sub>C</sub> (A) @ V <sub>CE</sub> & V <sub>BE(SAT)</sub> (V) Min	Process No.
TIP115	TO-220		60		1 mA	60	500	20,000	2	2.5		2					5J
TIP116	TO-220		80		1 mA	80	500	20,000	2	2.5		2					5J
TIP117	TO-220		100		1 mA	100	500	20,000	2	2.5		2					5J
TIP125	TO-220		60		200	60	1000	20,000	3	4.0		5					5J
TIP126	TO-220		80		200	80	1000	20,000	3	4.0		5					5J
TIP127	TO-220		100		200	100	1000	20,000	3	4.0		5					5J
2N6042	TO-220		100		500 <sup>†</sup>	100	1000	20,000	4	2.0		4	300				5K
SE9400	TO-220		60				750	20,000	1	2.0		4					5K
SE9401	TO-220		80				1000	20,000	4	2.5		7.5		1			5K
SE9402	TO-220		100				1000	20,000	7.5	2.0		4		1			5K
TIP105	TO-220		60				1000	20,000	3	2.0		3.0					5K
TIP106	TO-220		80				200	20,000	8	2.5		8.0					5K
TIP107	TO-220		100				1000	20,000	3	2.0		3					5K
TIP135	TO-220		60		200	60	1000	15,000	4	3.0		6	200				5K
TIP136	TO-220		80		200	80	1000	15,000	4	2.0		4	200				5K
TIP137	TO-220		100		200	100	1000	15,000	4	3.0		6	200				5K

NP Transistors

2